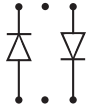


CMLD6001DO

SURFACE MOUNT
PICOmini™
DUAL, ISOLATED, OPPOSING
LOW LEAKAGE SILICON
SWITCHING DIODES

PICOmini™

SOT-563 CASE

Central™

Semiconductor Corp.

DESCRIPTION:
The CENTRAL SEMICONDUCTOR CMLD6001DO type contains Two (2) Isolated Opposing Configuration, Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a PICOmini™ surface mount package. These devices are designed for switching applications requiring extremely low leakage.

MARKING CODE: C60

MAXIMUM RATINGS: (T_A=25°C)

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Forward Surge Current, tp=1 µsec.
Forward Surge Current, tp=1 sec.
Power Dissipation
Operating and Storage
Junction Temperature
Thermal Resistance

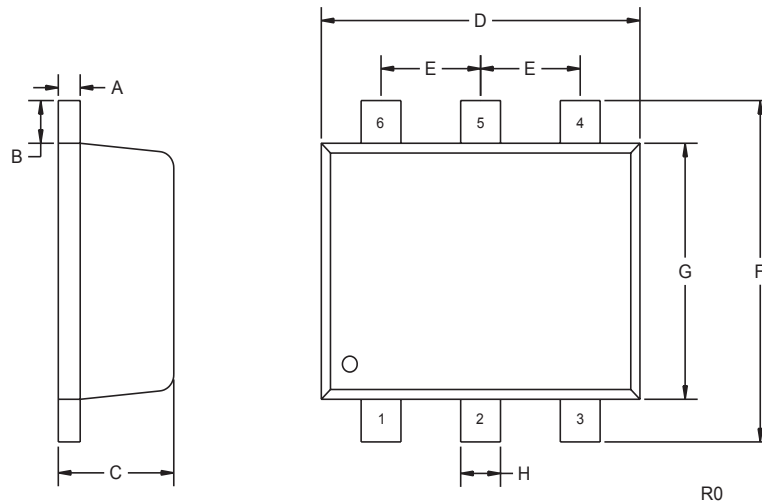
SYMBOL		UNITS
V _R	75	V
V _R RRM	100	V
I _F	250	mA
I _F FSM	4000	mA
I _F FSM	1000	mA
P _D	250	mW
T _J , T _{stg}	-65 to +150	°C
Θ _{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _R	V _R =75V		500	pA
BV _R	I _R =100µA	100		V
V _F	I _F =1.0mA		0.85	V
V _F	I _F =10mA		0.95	V
V _F	I _F =100mA		1.1	V
C _T	V _R =0, f=1 MHz		2.0	pF
t _{rr}	I _R =I _F =10mA, R _L =100Ω Rec. to 1.0mA		3.0	µs

**SURFACE MOUNT
PICOminiTM
DUAL, ISOLATED, OPPOSING
LOW LEAKAGE SILICON
SWITCHING DIODES**

SOT-563 CASE - MECHANICAL OUTLINE



LEAD CODE:

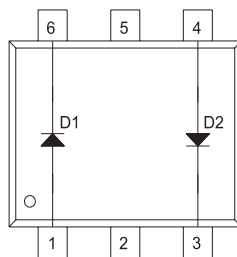
- 1) ANODE D1
- 2) NC
- 3) CATHODE D2
- 4) ANODE D2
- 5) NC
- 6) CATHODE D1

MARKING CODE: C60

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

Dual Opposing Configuration



R0 (3-November 2003)